Abstract

THROUGH-HOLE VIA ON SAW STREETS

A semiconductor device is manufactured by, first, providing a wafer designated with a saw street guide. The wafer is taped with a dicing tape. The wafer is singulated along the saw street guide into a plurality of dies having a plurality of gaps between each of the plurality of dies. The dicing tape is stretched to expand the plurality of gaps to a predetermined distance. An organic material is deposited into each of the plurality of gaps. A top surface of the organic material is substantially coplanar with a top surface of a first die of the plurality of dies. A plurality of via holes is formed in the organic material. Each of the plurality of via holes is patterned to each of a plurality of bond pad locations on the plurality of dies. A conductive material is deposited in each of the plurality of via holes. (FIG. 10B)